

Silicon PNP Power Transistors

2SA900

DESCRIPTION

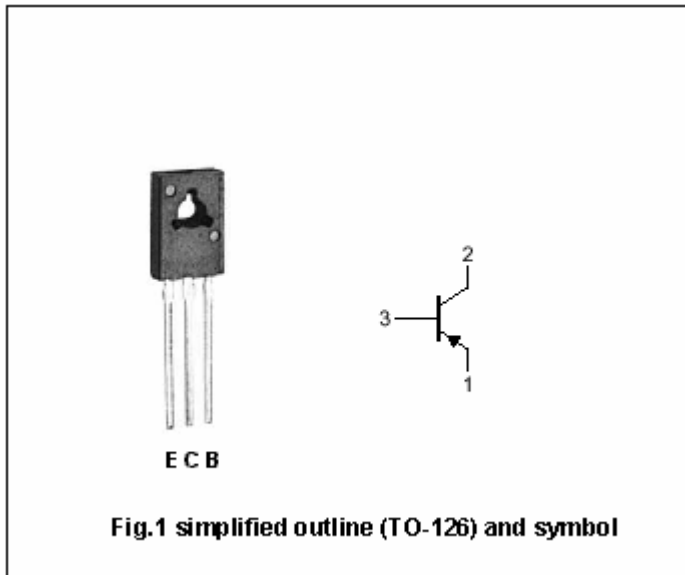
- With TO-126 package
- Complement to type 2SC1568
- Low collector saturation voltage

APPLICATIONS

- For audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-20	V
V_{CEO}	Collector-emitter voltage	Open base	-18	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
I_{CM}	Collector current-peak		-2	A
P_C	Collector power dissipation	$T_C=25$	1.2	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA; I _B =0	-18			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10 μ A ; I _E =0	-20			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10 μ A ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A ; I _B =-50mA			-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-500mA ; I _B =-50mA			-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-10V; I _E =0			-1	μ A
I _{CEO}	Collector cut-off current	V _{CE} =-18V; I _B =0			-10	μ A
h _{FE-1}	DC current gain	I _C =-500mA ; V _{CE} =-2V	90		470	
h _{FE-2}	DC current gain	I _C =-1.5A ; V _{CE} =-2V	50			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-6V; f=1MHz		40		pF
f _T	Transition frequency	I _E =50mA ; V _{CB} =-6V		200		MHz

◆ h_{FE-1} Classifications

Q	R	S	T	U
90-155	130-210	180-280	250-360	330-470

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PACKAGE OUTLINE

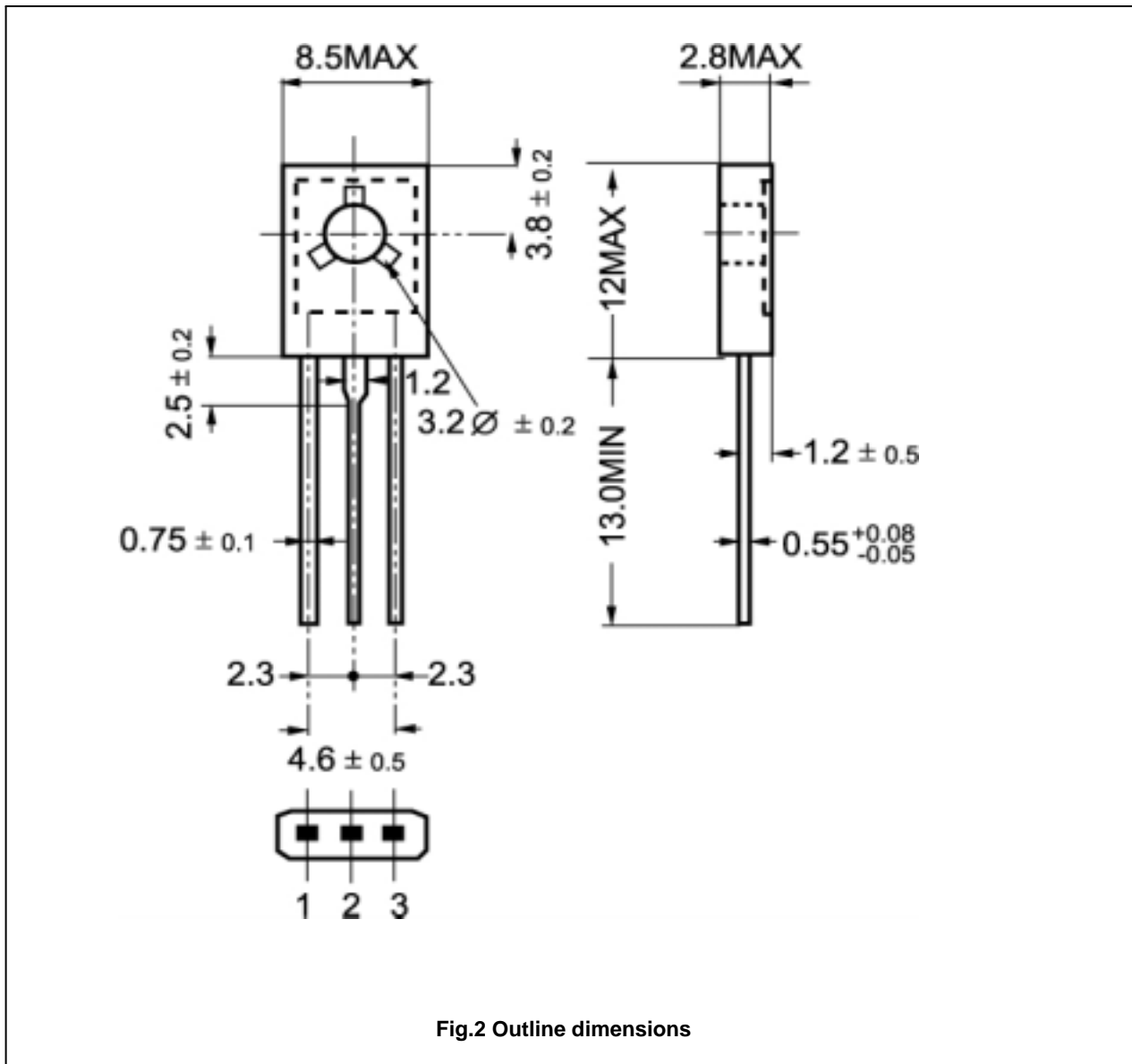


Fig.2 Outline dimensions